

### **Amendments to the Claims**

**1. (Currently Amended)** A method for manufacturing a semiconductor device comprising:

forming ~~an~~ a first N region and a P region on a substrate, forming wiring so as to connect one or both of the first N and the P regions; and

performing a processing step on a semiconductor substrate on which the upper surface of said wiring is exposed using a liquid applied to said semiconductor substrate and a light source radiating light onto said semiconductor substrate,

wherein said processing step is performed in a state in which the wavelength of light radiated onto said semiconductor substrate is 500 nm to less than 1  $\mu\text{m}$ , and

wherein said processing step is a cleaning step performed during, before or after a step that includes chemical mechanical polishing (CMP) for forming said wiring, said wavelength of light radiated onto said semiconductor substrate being 500 nm to less than 1  $\mu\text{m}$  in order to reduce an electromotive force at a PN junction in said semiconductor substrate, thereby inhibiting galvanic effects due to photoexcitation before, during or after said step including CMP, and preventing oxidation of a surface of said wiring.

**2. (Original)** A method according to claim 1, wherein said processing step is performed in a state in which said semiconductor substrate is grounded.

**3. (Canceled).**

4. **(Withdrawn)** A processing system comprising a processing unit that processes a semiconductor substrate using a liquid and a light source.
5. **(Withdrawn)** A processing system according to claim 4, wherein said light source radiates light having a wavelength of 500nm to less than 1  $\mu\text{m}$  onto said processing unit.
6. **(Withdrawn)** A processing system according to claim 4, wherein said processing unit provided with a rotating section that holds and rotates a semiconductor substrate, and a liquid supply section that supplies liquid to said semiconductor substrate, and said rotating section being grounded.
7. **(Withdrawn)** A processing system according to claim 5, wherein said processing unit provided with a rotating section that holds and rotates a semiconductor substrate, and a liquid supply section that supplies liquid to said semiconductor substrate, and said rotating section being grounded.
8. **(Withdrawn)** A semiconductor device comprising:  
  
a first N region and a P region formed on a substrate;  
  
wiring formed so as to connect either or both of these N and P regions; and  
  
the upper surface of said wiring being exposed to light,  
  
wherein a second N region is formed independent of said first N region on said substrate.

9. **(Withdrawn)** A semiconductor device according to claim 8, wherein the total surface area of said first N region and said second N region is 100 to 1/100 times the total surface area of said P region.
10. **(Withdrawn)** A semiconductor device according to claim 8, wherein said second N region is formed at the periphery of said substrate.
11. **(Withdrawn)** A semiconductor device according to claim 8, wherein said wiring has any one of Cu, Al and W as its main component.
12. **(Canceled).**
13. **(New)** A method according to claim 1, further comprising:  
  
forming on said substrate a second N region that is independent of said first N region.
14. **(New)** A method according to claim 13, wherein the total surface area of said first N region and said second N region is 100 to 1/100 times the total surface area of said P region.
15. **(New)** A method according to claim 13, wherein said second N region is formed at the periphery of said substrate.
16. **(New)** A method according to claim 13, wherein said wiring contains any one of Cu, Al and W as its main component.